

Customer No.: 31561
Application No.: 10/708,849
Docket No.: 12162-US-PA

In the Drawings:

In FIG.3A, please amend the drawing of the light emitting diode 350.

In FIG.3B, please amend “-V_T Writing Timing” to “V_T Writing Timing”.

In FIG.4A, please amend the drawing of the light emitting diode 450.

In FIG.4B, please amend the state of V_{ss} before the “V_T Writing Timing”.

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REMARKS

Applicants appreciate that the present invention has been allowed.

However, Applicants would like to amend editorial errors in specification and drawings.

Regarding the amendment addressed to the Specification

Amendments are made to Paragraphs [0046] and [0052].

In the amendments addressed to Paragraph [0046], Applicants revise the "source" terminal of the switching transistor 310 to the "drain" terminal of the switching transistor 310. The amendment is to make clear that at the data writing timing, the operational voltage V_{DD} is in a low state for turning off the light emitting diode 350, that is, no current is passed through the terminals of the operational voltage V_{DD} and the ground V_{SS} . The V_{scan} is remained at the high voltage level, which the transistor 310 is remained turned on. The data voltage V_{data} from the signal line 310b is electrically connected to the drain terminal of the switching transistor 310, and as shown in FIG.3B, the voltage level of the V_G is changed to the data voltage V_{data} from the signal line 310b.

In the amendments addressed to Paragraph [0052], Applicants revise the "source" terminal of the switching transistor 410 to the "drain" terminal of the switching transistor 410 with the same reason set forth above.

It is believed that no new matter is introduced with the amendments.

Regarding the amendment addressed to the Drawings

Amendments are made to FIGs. 3A, 3B, 4A and 4B. More particularly, in FIGs3A and

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4A, the drawing of the light emitting diode 350 and 450 are amendment to meet the drawing of the diode, which can be supported in the drawings of the diodes 130 and 240 respectively in FIGs.1 and 2.

Amendment is made to FIG 3B that the description “-V_T Writing Timing” is amended to “V_T Writing Timing” to correct some typographical error, which can be supported in Para. [0045] of the Specification, for example, “a threshold voltage V_T is applied to the capacitor 340 at a threshold voltage writing time”, and also be supported in FIG.4B.

Amendment is made to FIG 4B that the state of V_{SS} before the “V_T Writing Timing” is in a low voltage level, which is supported in Para. [0051] of the Specification stated that “At the beginning of the V_T writing timing, the scanning signal voltage V_{scan} on the scan line 410a is raised from a low voltage level to a high voltage level for turning on the switching transistor 410. The V_{SS} rises to a high voltage level.” The V_{SS} is at the low voltage level and at the beginning of the V_T writing timing, the V_{SS} rises to the high voltage level.

Applicants respectfully submit that the amendments embodied in the specification and in the drawings do not introduce new matters or new issues and do not change the scope thereof. The proposed amendments also require now additional search or examination.

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Respectfully submitted,

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